THIS SHEET HAS BEEN REPLACED

ST 9710 /Dr. Ei

Process for etching semiconductor wafers

Abstract

The invention relates to a process for etching semiconductor wafers with an etching mixture which is obtained by mixing nitric acid and hydrofluoric acid and optionally a surfactant and to which either further hydrofluoric acid or further hydrofluoric acid and nitric acid is/are added. Nitric acid having a concentration of ≥ 70% by weight and hydrofluoric acid having a concentration of > 50% by weight, or nitric acid having a concentration of > 70% by weight and hydrofluoric acid having a concentration of ≥ 50% by weight are used to prepare the etching mixture.

This Sheet Has Been Replaced